

Component Specifications for a Re-Configurable Multi Mode Receiver



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The authors would like to thank the European Community where this R&D work is being supported under the contract number IST-2001-34561.

For further information please refer to www.mumor.org.



Overview

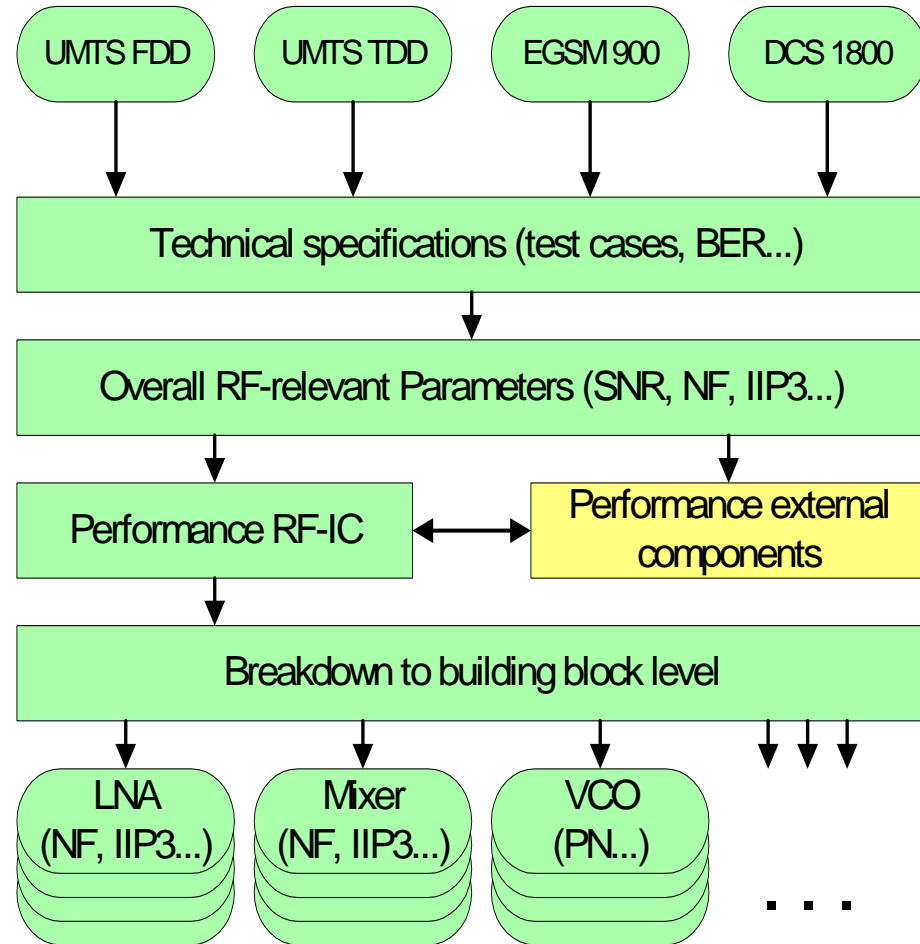
- Design Process: From BER to SNR
- Overall RF-Performance
- Self blocking in the UMTS FDD mode
- Breakdown to Building Block Level
- Comparison: Specification – Measured Performance

Design Process

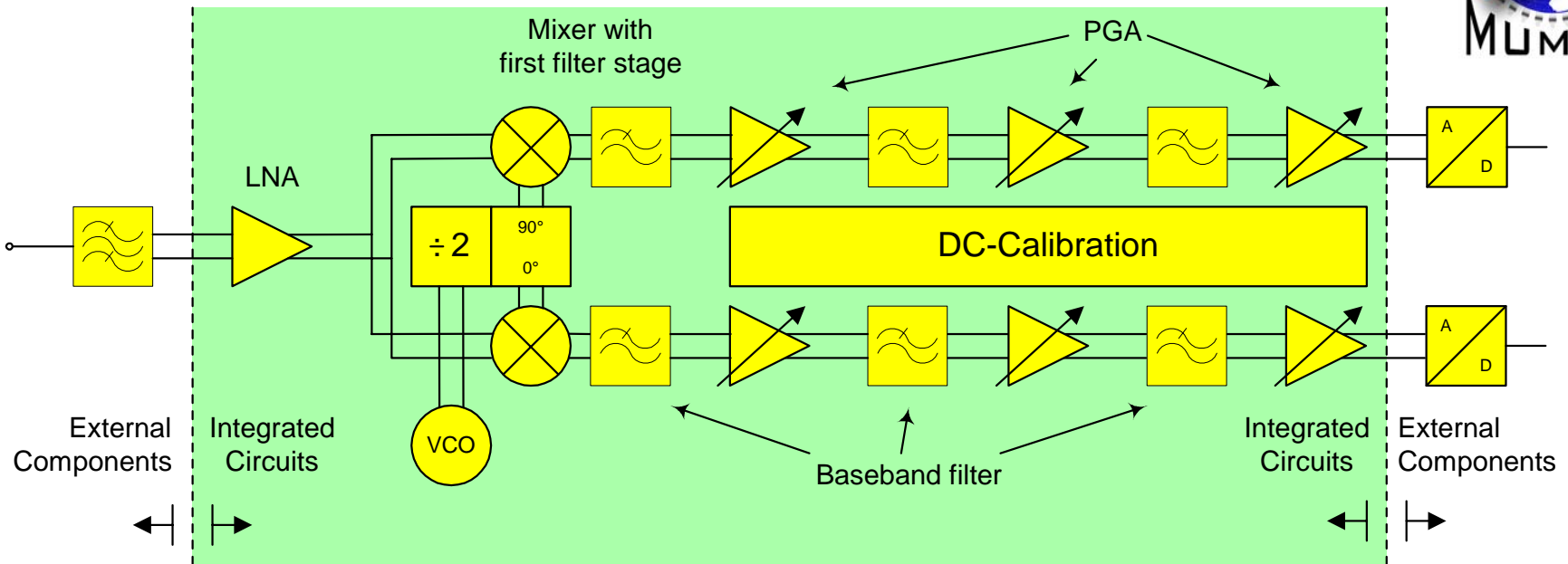


Technical Specifications

- UMTS FDD:
3GPP TS 25.101 v 5.2.0
- UMTS TDD:
3GPP TS 25.102 v 5.0.1
- GSM, DCS:
ETSI GSM 05.05 v 8.4.0



Design Process



LNA: Noisefigure, IIP3, IIP2...

Mixer: Noisefigure, IIP3, IIP2...

...





- **Problem:**

Test cases specified by Bit Error Rates that shall not be exceeded. $BER < 0.001$ contains no information about RF performance.

- **Solution:**

Find relation between BER and SNR by baseband simulation or estimation from test cases described in the specifications.



UMTS FDD and TDD:

- For all test cases the BER shall not exceed 0.001
- All test cases use the same DL reference channel
- Test case maximum input level employs well defined signal- and interferer-level
- Signal and interferer definitely exceed all other noise sources
- Interferer can be regarded as noise



UMTS FDD:

Test case maximum input power

$$\frac{DPCH_Ec}{I_{or}} = -19dB$$

Energy per chip in DPCH over total power spectral density

$$\hat{I}_{or} = -25 \frac{dBm}{3.84MHz}$$

Total received power spectral density

$$\frac{S}{I} = \frac{\frac{DPCH_Ec}{I_{or}}}{1 - \frac{DPCH_Ec}{I_{or}}} = \frac{10^{\frac{19}{10}}}{1 - 10^{\frac{19}{10}}} = 0.0127 \Leftrightarrow SNR = -18.9 \text{ dB}$$

From BER to SNR



EGSM 900 / DCS 1800:

Test case cochannel interference

$$C/I_c = 9 \text{ dB} \quad \Rightarrow \quad \text{SNR} = 9 \text{ dB}$$

Mode	UMTS FDD	UMTS TDD	GSM DCS
SNR	-18.9 dB	-6 dB	9 dB



Overall RF-Performance



Mode	SNR	NF_{\max}	$IIP2_{\min}$	$IIP3_{\min}$
UMTS FDD	-18.9 dB (spread spectrum)	9.6 dB	8 dBm	-21.3 dBm
UMTS TDD	-6 dB (spread spectrum)	9.2 dB	8 dBm	-20.9 dBm
EGSM 900	9 dB	10 dB	43 dBm	-18 dBm
DCS 1800	9 dB	10 dB	43 dBm	-18 dBm

Overall RF-Performance



Mode	P_{\min}	P_{\max}	$A_{V,\min}$	$A_{V,\max}$
UMTS FDD	-117 dBm	-25 dBm	22 dB	95 dB
UMTS TDD	-105 dBm	-25 dBm	10 dB	83 dB
EGSM 900	-102 dBm	-15 dBm	-7 dB	80 dB
DCS 1800	-102 dBm	-23 dBm	1 dB	80 dB



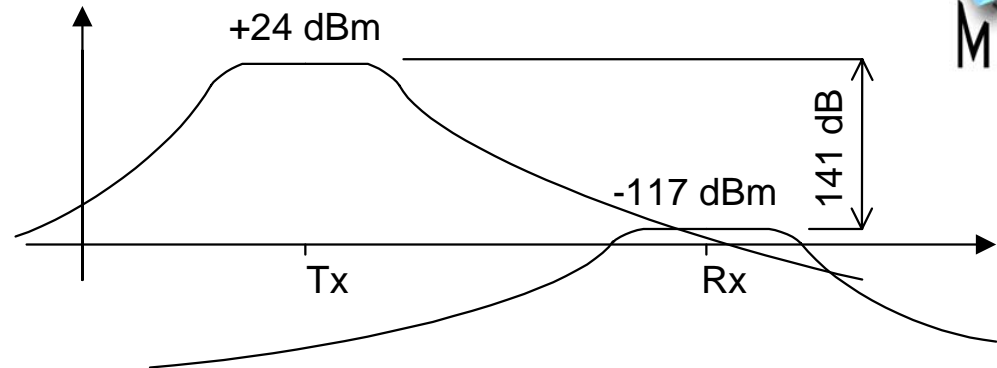
Problem:

Transmit signal:

+24 dBm at f_{TX}

Received signal:

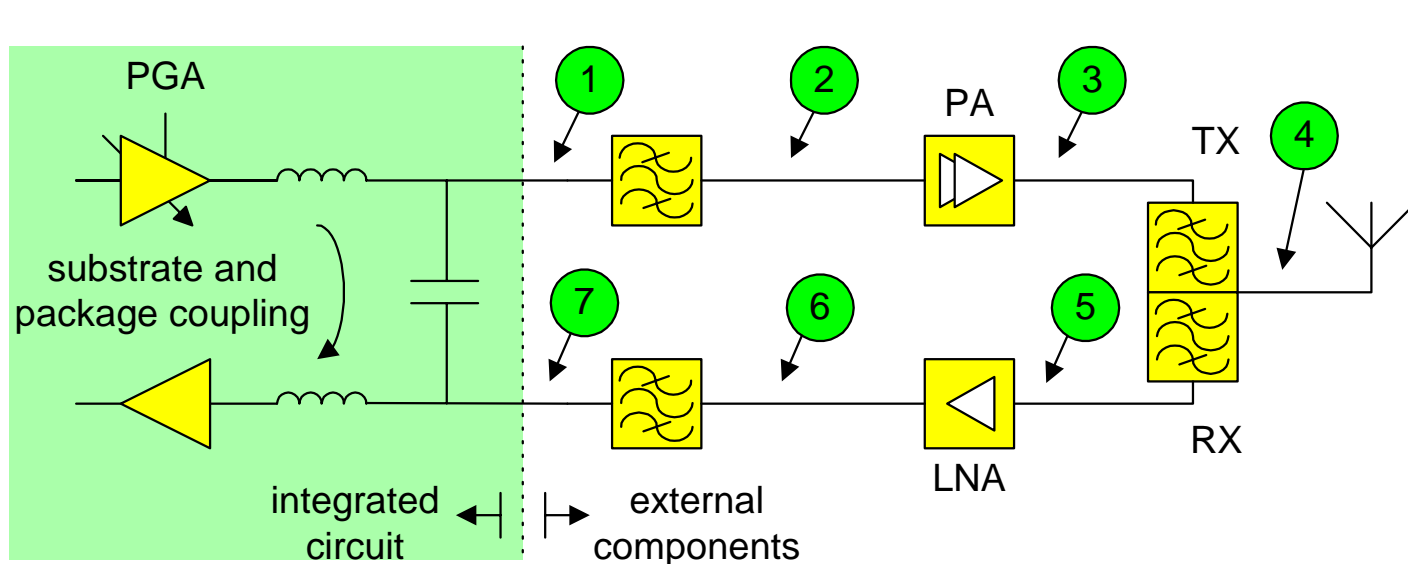
-117 dBm at f_{RX}



The TX-Signal itself is a blocking signal for the receiver

The noise sidebands of the signal shall be considerably below the thermal noise floor

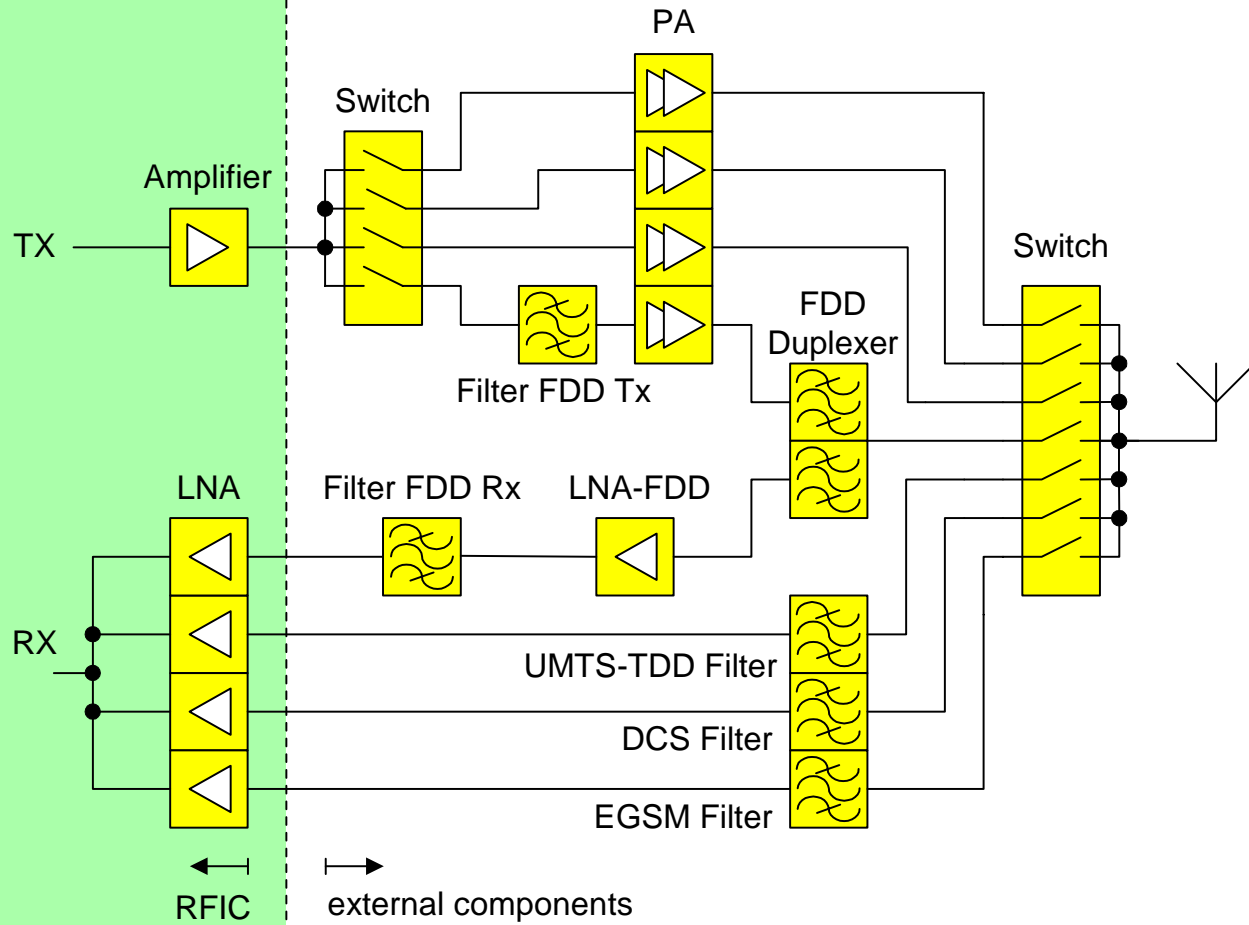
UMTS FDD



	1. PGA out	2. Filter out	3. PA out	4. Antenna	5. LNA in	6. Filter in	7. Amp. in
Signal Rx				-117 dBm	-120 dBm	-105 dBm	-109 dBm
Signal Tx	+1 dBm	-2.5 dBm	25.5 dBm	24 dBm	-23 dBm	-8 dBm	-38 dBm
$N_{TX} @ f_{RX}$	-147 dBm/Hz	-174 dBm/Hz	-136 dBm/Hz	-174 dBm/Hz	-174 dBm/Hz	-157 dBm/Hz	-160.7 dBm/Hz



Re-configurable Front End



Blocking Performance



- **Out of band blocking**

Blocking Performance Blockers outside the desired band can be attenuated by front end filters

- **In band blocking**

Blockers inside the desired band can be attenuated by a channel filter at baseband frequency

- **Adjacent channel selectivity (ACS)**

Blockers in adjacent channels are too close for a considerable attenuation by the baseband filter



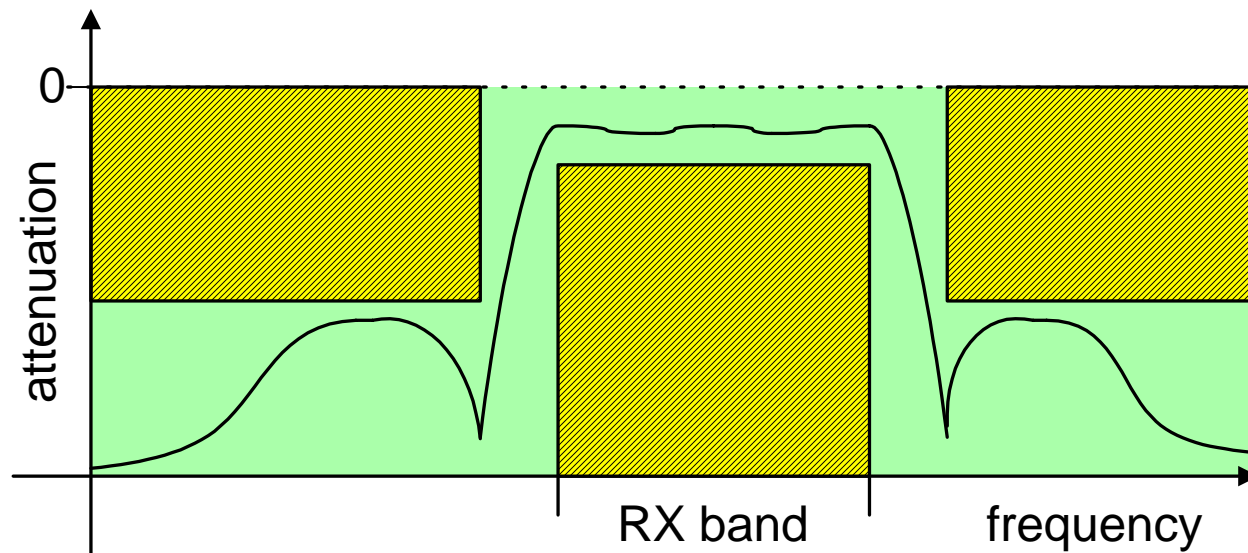
Blocking Performance



Out of band blockers specify the frontend filters

Blockers outside the desired band have to be attenuated to a level comparable to in band blockers

Frontend bandpass filter

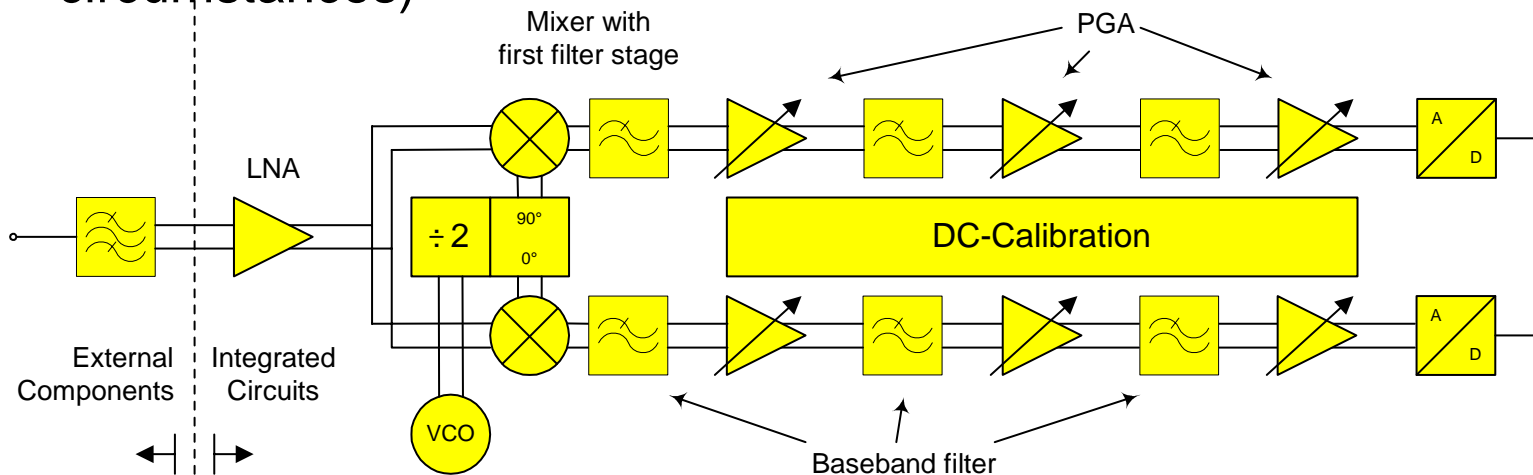


Blocking Performance

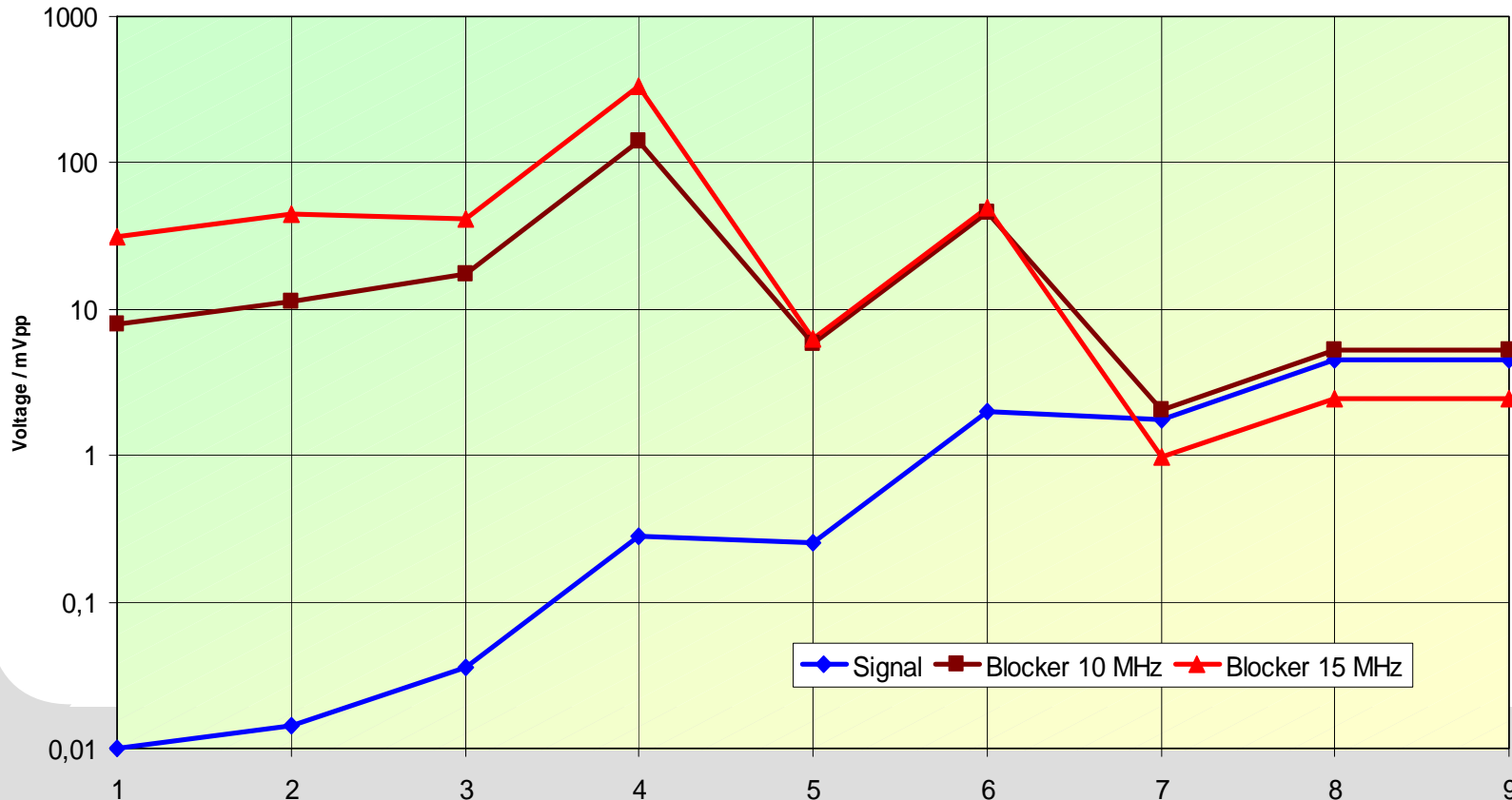
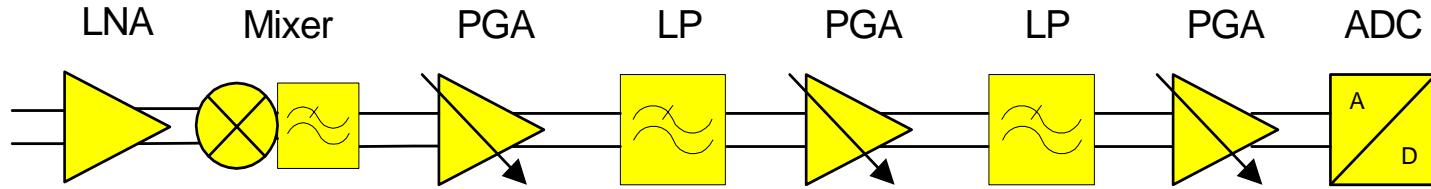


In band blocker

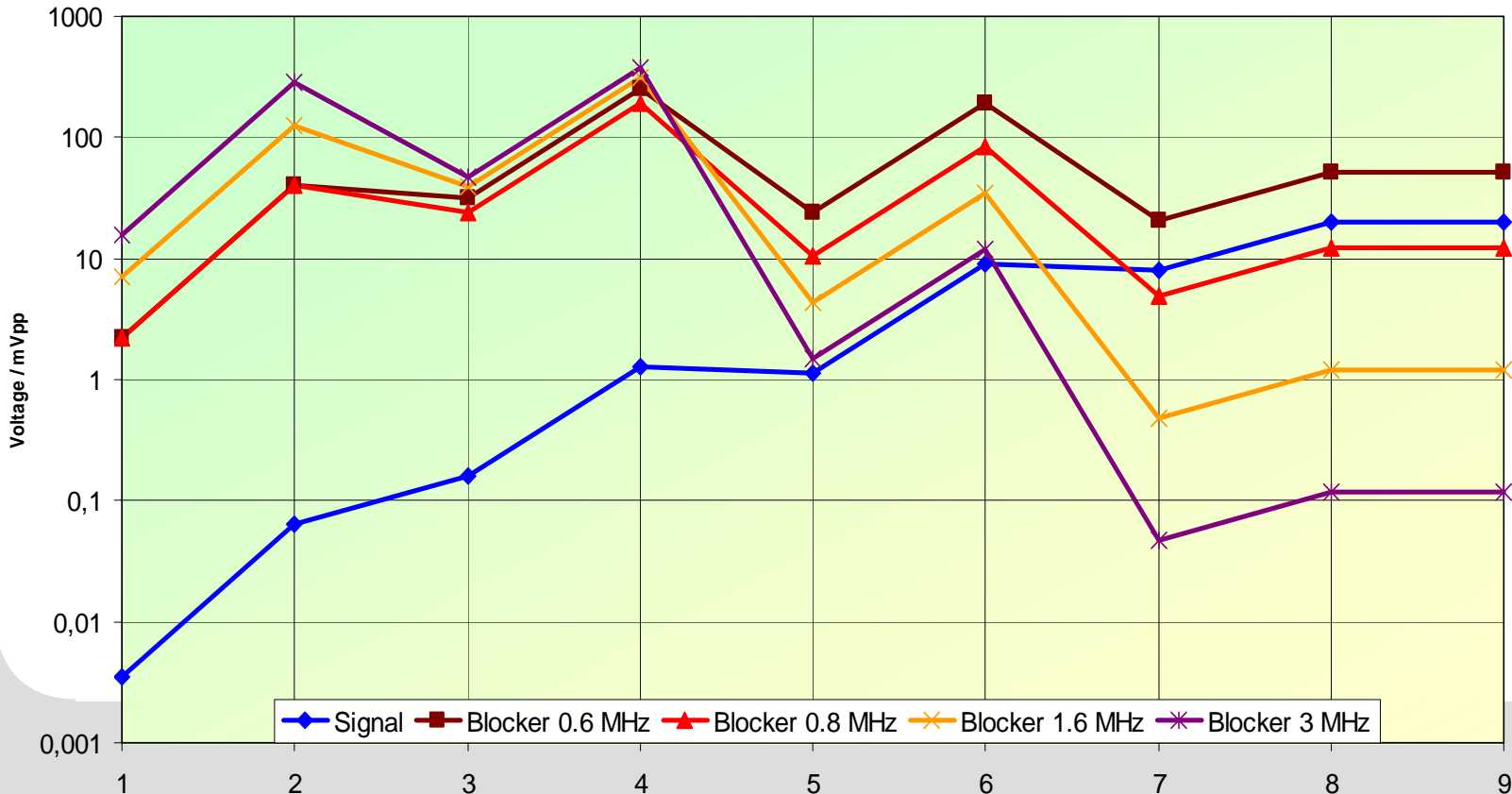
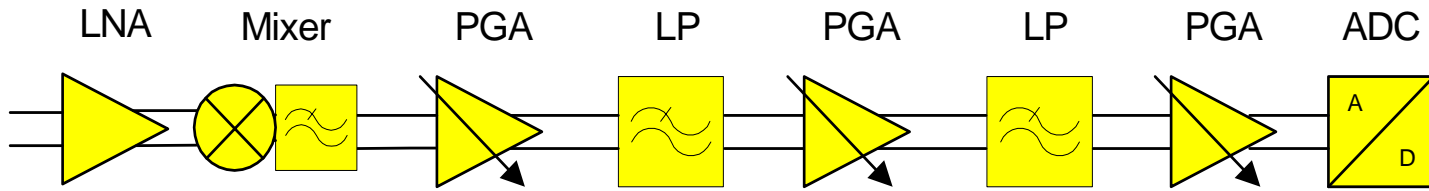
- Specify linearity of the front end stages (LNA...)
- Specify the characteristic of the baseband filter
- Gain partitioning for every input level has to be planned (no stage must be driven into saturation under any circumstances)



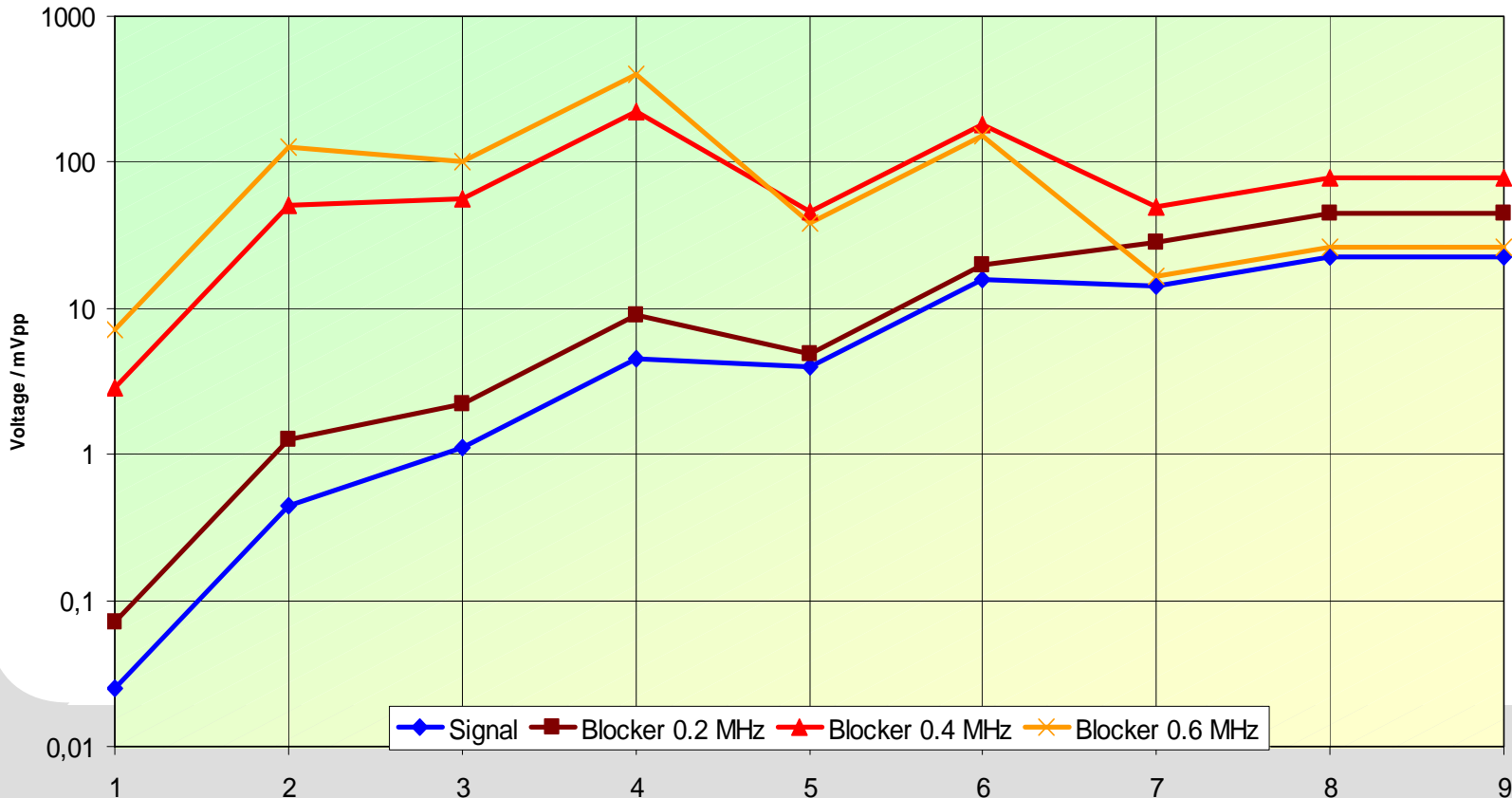
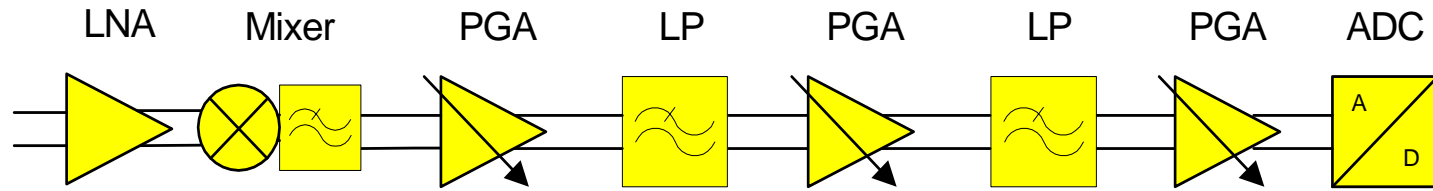
Example Blocking UMTS FDD



Example Blocking DCS



Example Adjacent Channel Selectivity DCS



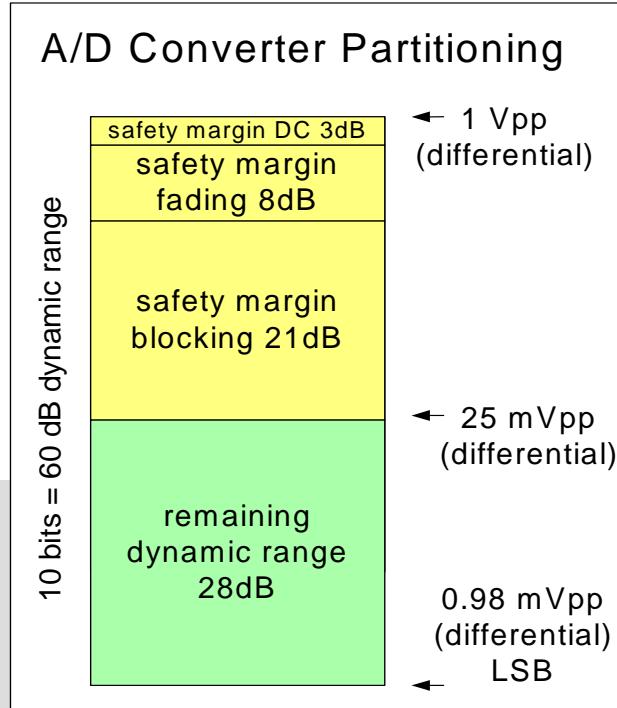
Blocking Performance



Adjacent channel performance GSM / DCS

Wanted signal: -82 dBm

- Cochannel interference: $C/I_c = 9 \text{ dB}$
- Adjacent channel (200 kHz) interference: $C/I_{a1} = -9 \text{ dB}$
- Adjacent channel (400 kHz) interference: $C/I_{a1} = -41 \text{ dB}$
- Adjacent channel (600 kHz) interference: $C/I_{a1} = -49 \text{ dB}$



Interferer at 400 kHz and 600 kHz offset can not be attenuated sufficiently to be neglected. At the end of the receiver chain residual interferer is considerably above the desired signal.

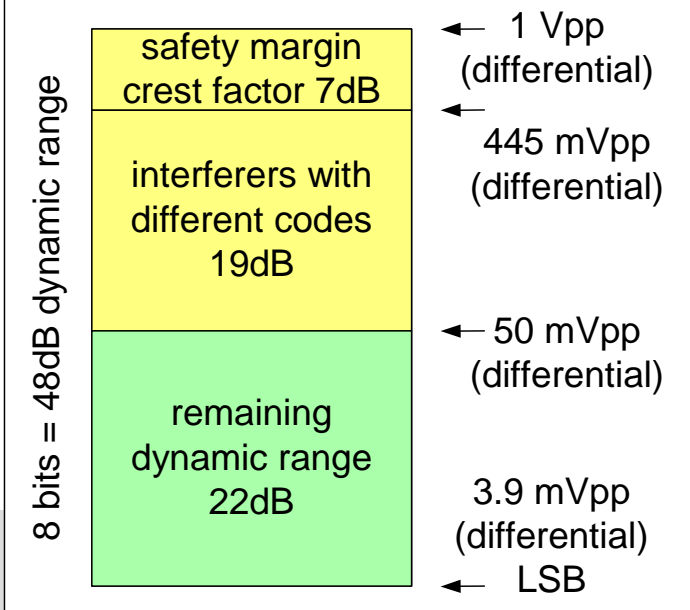


UMTS FDD: Maximum input power test case



$$\frac{DPCH_{-}Ec}{I_{or}} = -19dB \quad \hat{I}_{or} = -25 \frac{dBm}{3.84MHz}$$

A/D Converter Partitioning



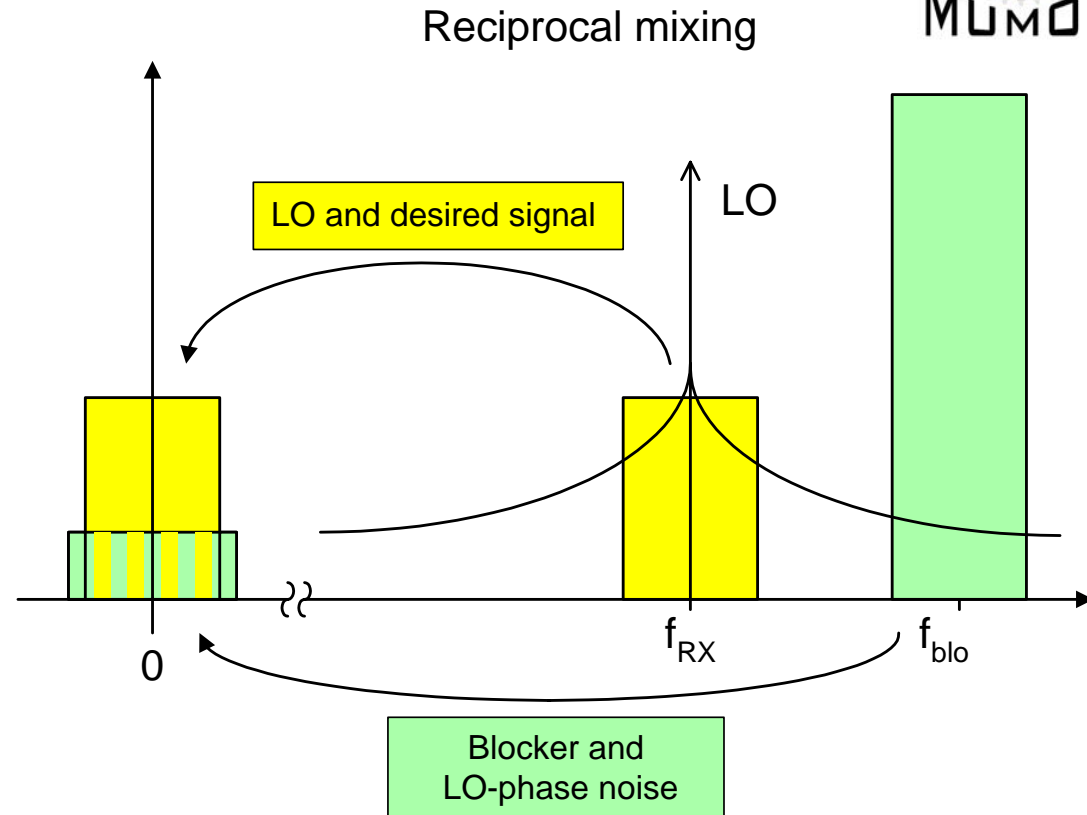
- -44 dBm useful data at f_{RX}
 \Rightarrow 50 mVpp
- -25 dBm received signal at f_{RX}
 \Rightarrow 445 mVpp

LO phase noise



LO and desired signal at f_{RX} produce a signal at baseband frequency

Blocker and LO-phase noise produce noise at baseband frequency



LO phase noise



UMTS FDD:

Offset: Phase noise:

5 MHz -97.8 dBc/Hz

10 MHz -94.6 dBc/Hz

15 MHz -106.6 dBc/Hz

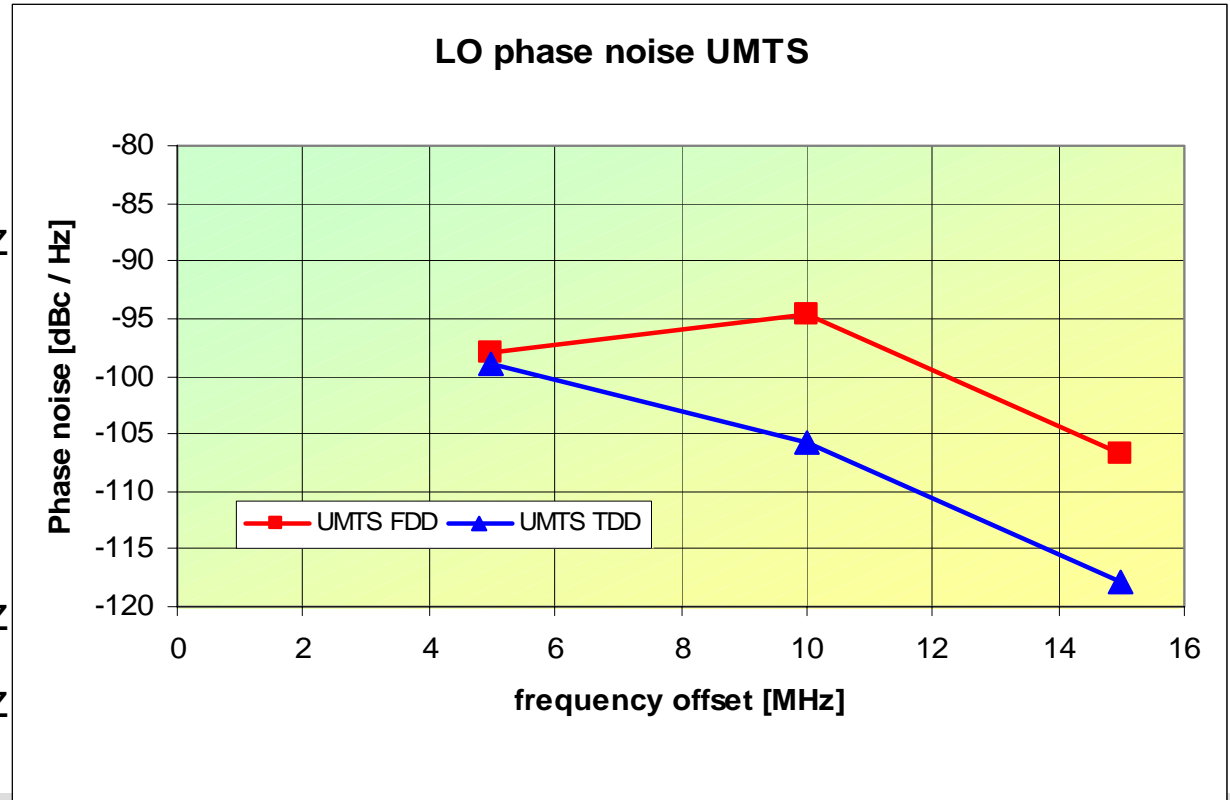
UMTS TDD:

Offset: Phase noise:

5 MHz -98.8 dBc/Hz

10 MHz -105.9 dBc/Hz

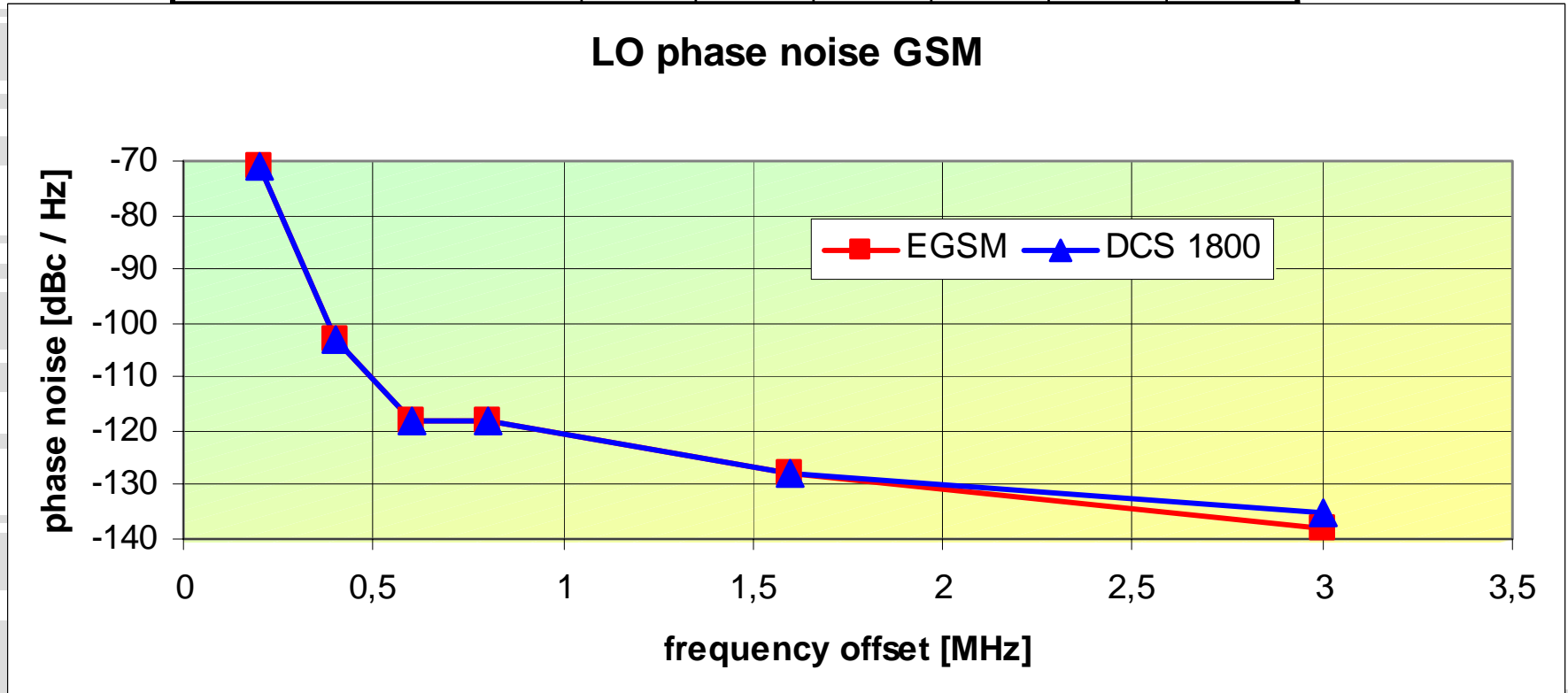
15 MHz -117.8 dBc/Hz



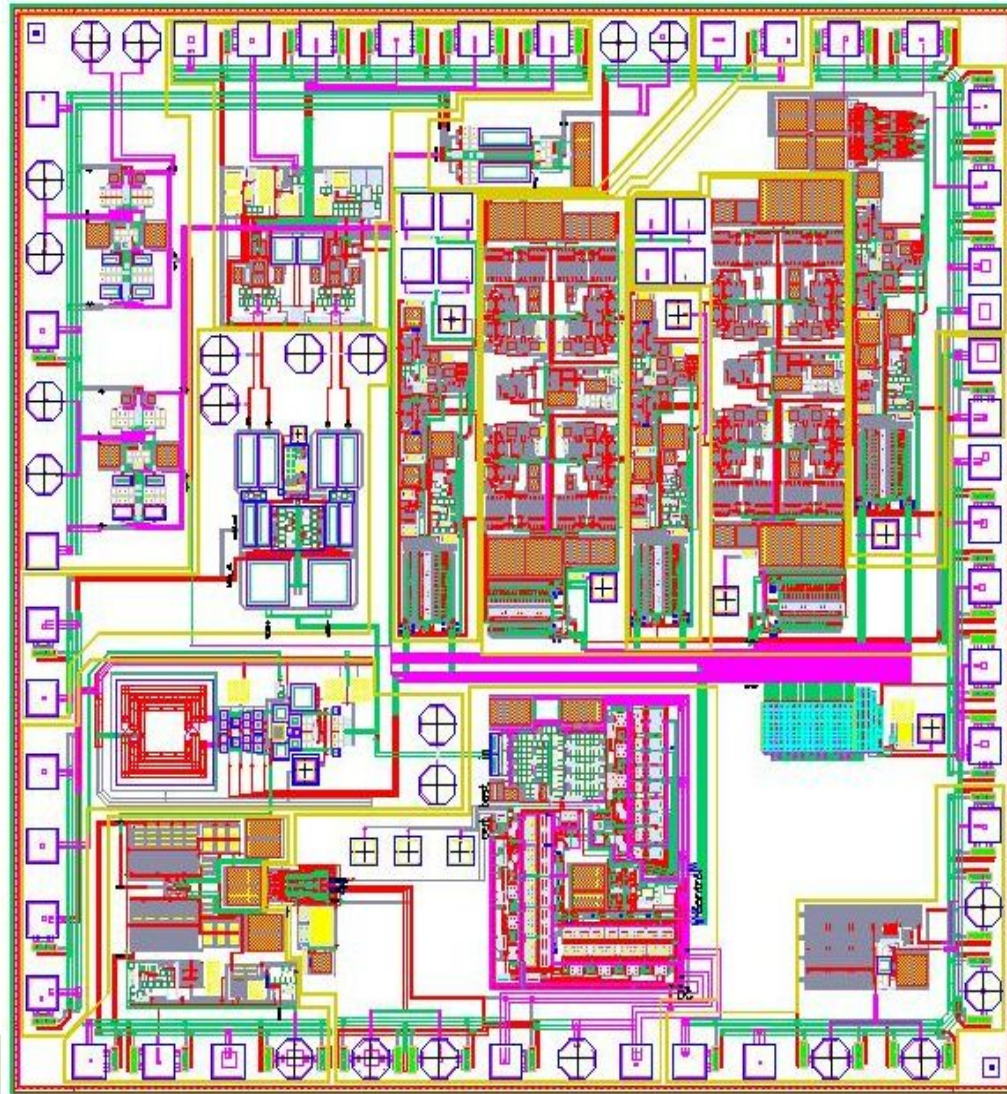
LO phase noise



Offset / MHz	0.2	0.4	0.6	0.8	1.6	3
PN EGSM / dBc/Hz	-71	-103	-118	-118	-128	-138
PN DCS / dBc/Hz	-71	-103	-118	-118	-128	-135



Realised RF-IC



Realised Receiver Chip:

- Process: BiCMOS 0.35 μ m
- $f_T = 50$ GHz
- Chip Area: 2.5mm x 2.5mm



LNA:

Noise Figure, Gain, IIP3 within the specifications



VCO and Scaler:

Phase noise within the specifications for UMTS FDD and UMTS TDD.

Phase noise for GSM not within the specifications.

Cause: Noise produced in the voltage regulator.

Conclusion

- RF specifications can be derived from test cases described in standards
- Negative effects do not occur independently from each other
- The derived RF specifications for the building blocks are starting values for an iterative process
- Achievable performance of building blocks have to be considered for the next iteration

